

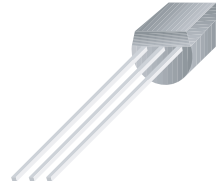
**PNP SILICON PLANAR EPITAXIAL
HIGH VOLTAGE VIDEO TRANSISTORS**
High Voltage Video Amplifier

Darlington Transistor

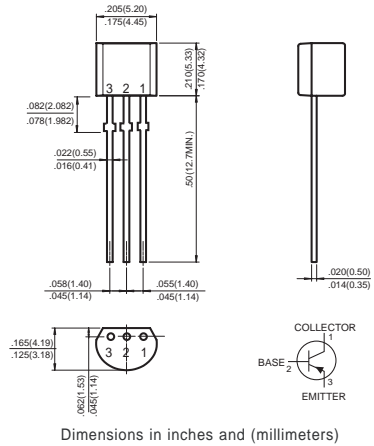
* Power Dissipation: $P_D=625\text{mW}$

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified.



TO-92



Absolute Maximum Ratings $T_A=25\text{ }^\circ\text{C}$ unless otherwise noted

DESCRIPTION	SYMBOL	BF491	BF492	BF493	UNITS
Collector-Emitter Voltage	V_{CE0}	200	250	300	Volts
Collector Base Voltage	V_{CB0}	200	250	300	Volts
Emitter Base Voltage	V_{EB0}	6	8	8	Volts
Collector Current Continuous	I_C		500		mAmps
Total Device Dissipation @ $T_A=25\text{ }^\circ\text{C}$ Derate Above 25°C	P_D		625 1.2		mW mW/°C
Total Device Dissipation @ $T_C=25\text{ }^\circ\text{C}$ Derate Above 25°C	P_D		1500 12		mW mW/°C
Operating And Storage Junction Temperature Range	T_J, T_{STG}		-55 to + 150		°C

ELECTRICAL CHARACTERISTICS $T_A=25\text{ }^\circ\text{C}$ unless otherwise noted

DESCRIPTION	Test Condition	SYMBOL	BF491	BF492	BF493	UNITS
Collector-Base Breakdown Voltage	$I_C=0.1\text{ mA}, I_E=0$	BV_{CB0}	>200	>250	>300	Volts
Collector-Emitter Breakdown Voltage	$I_C=1\text{ mA}, I_B=0$	BV_{CE0}^*	>200	>250	>300	Volts
Emitter-Base Breakdown Voltage	$I_E=100\text{ uA}, I_C=0$	BV_{EB0}	>6.0	>8.0	>8.0	Volts
Collector Cutoff Current	$V_{CB}=160\text{ V}, I_E=0$ $V_{CB}=200\text{ V}, I_E=0$	I_{CB0}	<0.1	<0.1	<0.1	uA
Emitter Cutoff Current	$V_{EB}=4.0\text{ V}, I_C=0$ $V_{EB}=6.0\text{ V}, I_C=0$	I_{EB0}	<0.1	<0.1	<0.1	uA
DC Current Gain	$I_C=1\text{ mA}, V_{CE}=10\text{ V}$ $I_C=10\text{ mA}, V_{CE}=10\text{ V}$	h_{FE}	>25 >40	>25 >40	>25 >40	
Collector-Emitter Saturation Voltage	$I_C=20\text{ mA}, I_B=2\text{ mA}$	$V_{CE(sat)}$	<2	<2	<2	Volts
Base-Emitter Saturation Voltage	$I_C=20\text{ mA}, I_B=2\text{ mA}$	$V_{BE(sat)}$	<2	<2	<2	Volts

ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless specified otherwise)

DESCRIPTION	SYMBOL	TEST CONDITION	BF491	BF492	BF493	UNITS
Current Gain-Bandwidth Product	f_T	$I_C=10\text{mA}$, $V_{CE}=20\text{V}$, $f=20\text{MHz}$	>50	>50	>50	MHz
Feedback Capacitance	C_{re}	$V_{CB}=100\text{V}$, $f=1\text{MHz}$, $I_E=0$	<2	<2	<2	pF

*Pulse Condition: = Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2.0\%$.

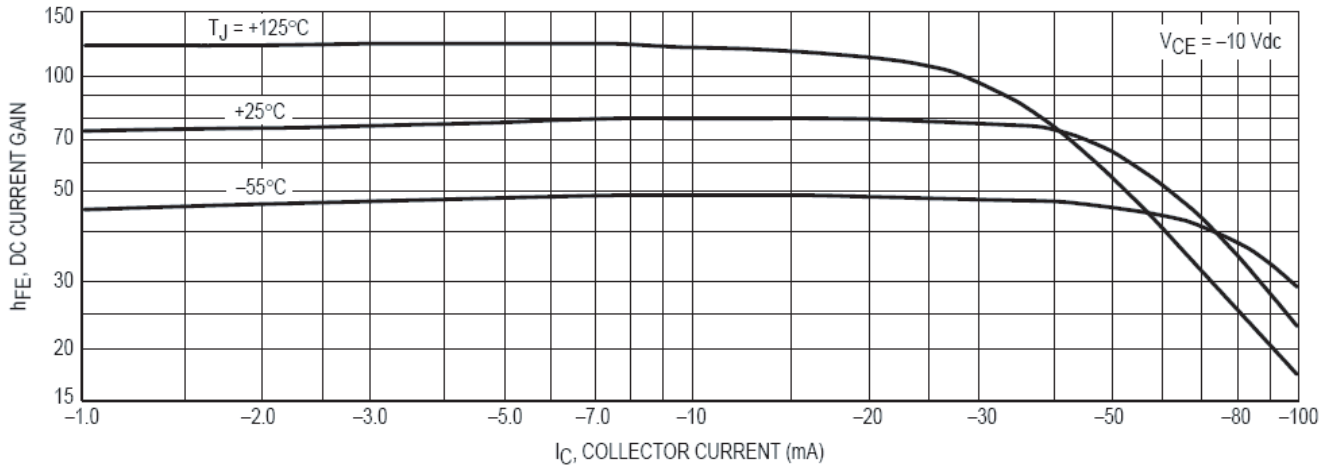


Figure 1. DC Current Gain

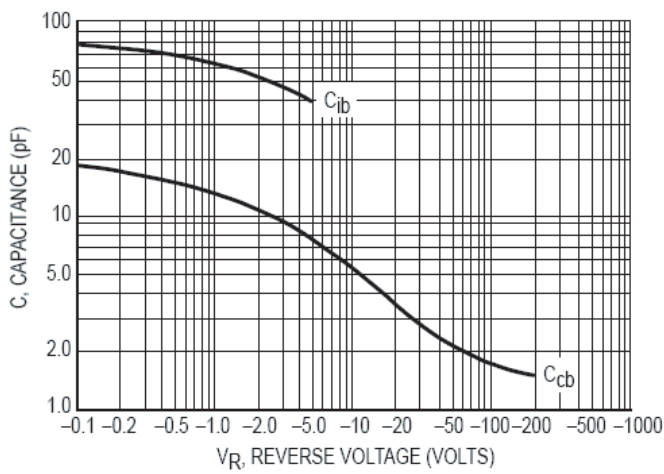


Figure 2. Capacitances

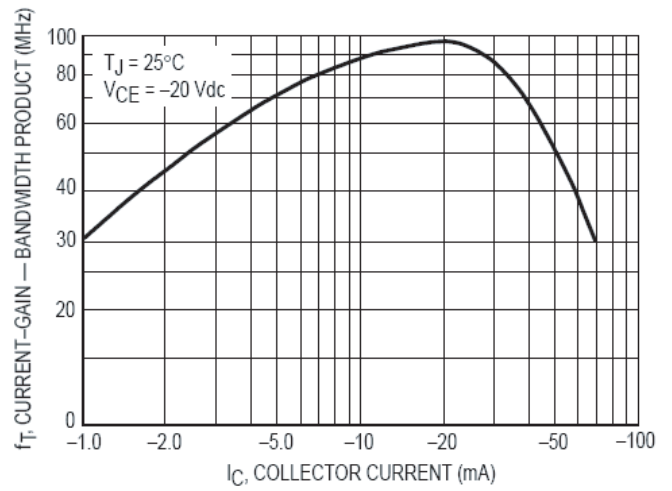


Figure 3. Current-Gain — Bandwidth Product

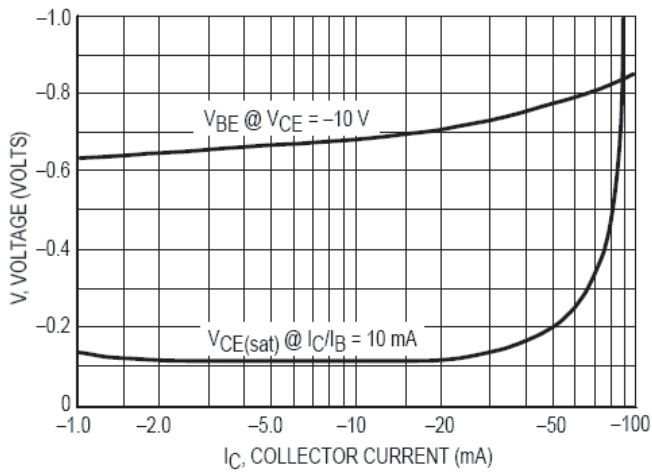


Figure 4. "On" Voltages

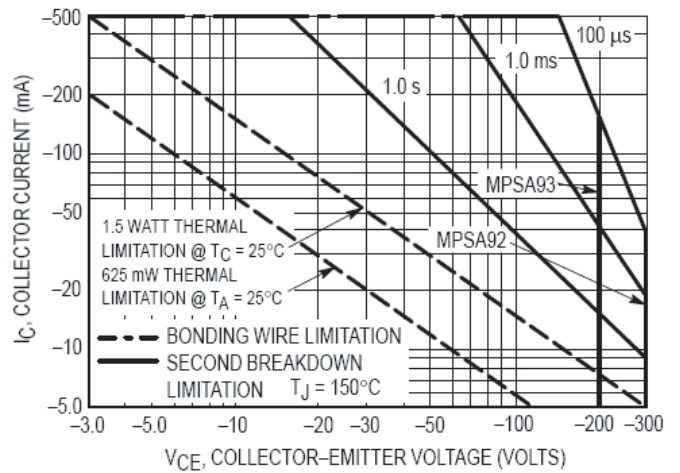


Figure 5. Active Region — Safe Operating Area

DISCLAIMER NOTICE

Rectron Inc reserves the right to make changes without notice to any product specification herein, to make corrections, modifications, enhancements or other changes. Rectron Inc or anyone on its behalf assumes no responsibility or liability for any errors or inaccuracies. Data sheet specifications and its information contained are intended to provide a product description only. "Typical" parameters which may be included on RECTRON data sheets and/ or specifications can and do vary in different applications and actual performance may vary over time. Rectron Inc does not assume any liability arising out of the application or use of any product or circuit.

Rectron products are not designed, intended or authorized for use in medical, life-saving implant or other applications intended for life-sustaining or other related applications where a failure or malfunction of component or circuitry may directly or indirectly cause injury or threaten a life without expressed written approval of Rectron Inc. Customers using or selling Rectron components for use in such applications do so at their own risk and shall agree to fully indemnify Rectron Inc and its subsidiaries harmless against all claims, damages and expenditures.